

N-Channel 100 V (D-S) MOSFET

| PRODUCT SUMMARY | | |
|---------------------|---------------------------------|--------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) |
| 100 | 0.110 at V _{GS} = 10 V | 15 |
| | 0.115 at V _{GS} = 6 V | 15 |

FEATURES

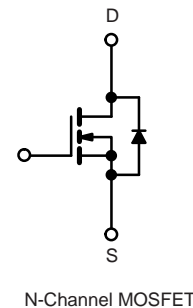
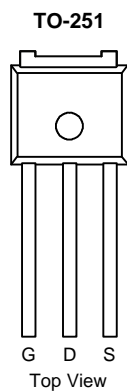
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested



RoHS
COMPLIANT

APPLICATIONS

- Primary Side Switch



| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | |
|---|-------------------------|-----------------------------------|------------------|------|
| Parameter | | Symbol | Limit | Unit |
| Drain-Source Voltage | | V _{DS} | 100 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 175 °C) ^b | T _C = 25 °C | I _D | 15 | A |
| | T _C = 125 °C | | 8.7 | |
| Pulsed Drain Current | | I _{DM} | 45 | |
| Continuous Source Current (Diode Conduction) | | I _S | 15 | |
| Avalanche Current | | I _{AR} | 15 | |
| Repetitive Avalanche Energy (Duty Cycle ≤ 1 %) | L = 0.1 mH | E _{AR} | 11.3 | mJ |
| Maximum Power Dissipation | T _C = 25 °C | P _D | 61 ^b | W |
| | T _A = 25 °C | | 2.7 ^a | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 175 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------------|--------------|-------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Junction-to-Ambient ^a | t ≤ 10 s | R _{thJA} | 16 | 20 | °C/W |
| | Steady State | | 45 | 55 | |
| Junction-to-Case | | R _{thJC} | 2 | 2.4 | |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

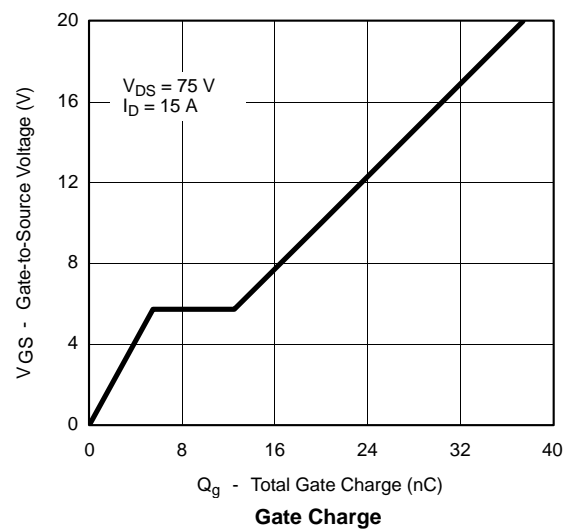
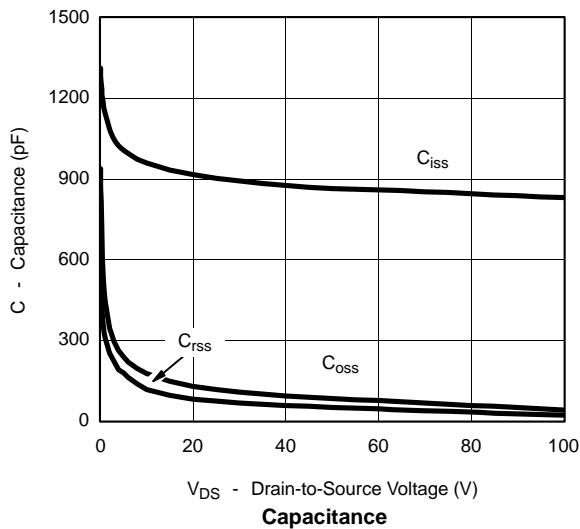
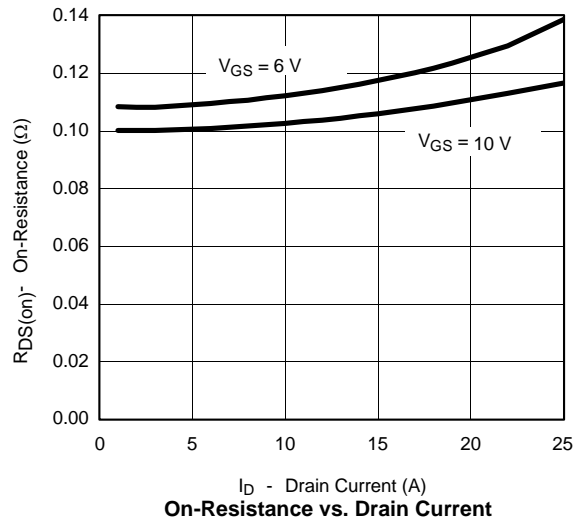
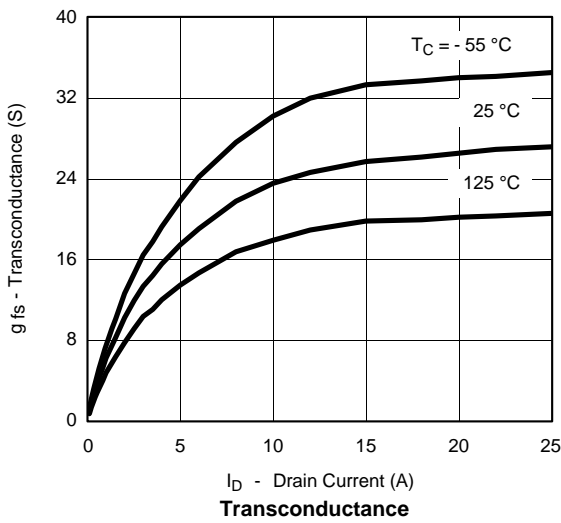
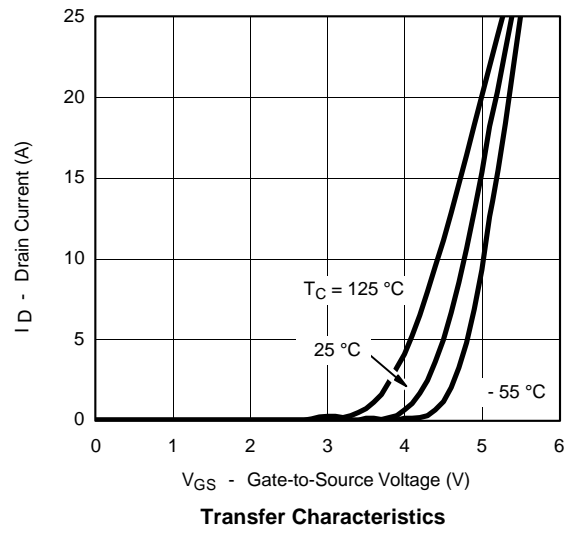
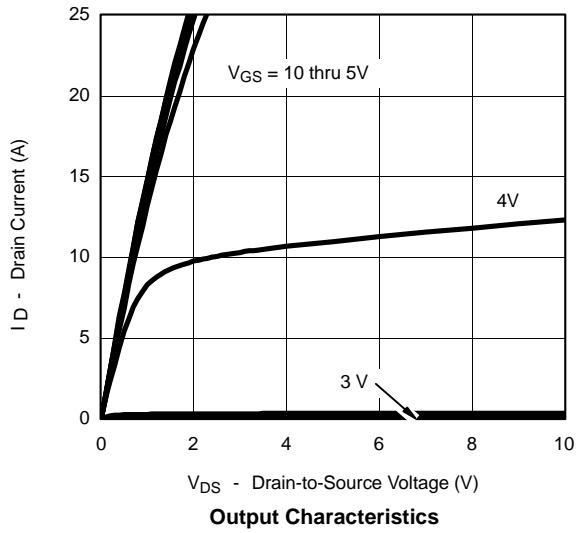
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|---|--------------|--|------|-------------------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. ^a | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 1.0 | | 3.0 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | | 50 | |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$ | | | 250 | |
| On-State Drain Current ^b | $I_{D(on)}$ | $V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$ | 15 | | | A |
| Drain-Source On-State Resistance ^b | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | | 0.110 | | Ω |
| | | $V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 0.170 | | |
| | | $V_{GS} = 10\text{ V}, I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$ | | 0.230 | | |
| | | $V_{GS} = 6\text{ V}, I_D = 10\text{ A}$ | | 0.115 | | |
| Forward Transconductance ^b | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 15\text{ A}$ | | 25 | | S |
| Dynamic^a | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 892 | | μF |
| Output Capacitance | C_{oss} | | | 110 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 70 | | |
| Total Gate Charge ^c | Q_g | $V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | | 20 | 25 | nC |
| Gate-Source Charge ^c | Q_{gs} | | | 5.5 | | |
| Gate-Drain Charge ^c | Q_{gd} | | | 7 | | |
| Gate Resistance | R_g | | 1 | | 3.2 | Ω |
| Turn-On Delay Time ^c | $t_{d(on)}$ | $V_{DD} = 75\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong 15\text{ A}, V_{GEN} = 10\text{ V}, R_G = 2.5\text{ }\Omega$ | | 8 | 12 | ns |
| Rise Time ^c | t_r | | | 35 | 55 | |
| Turn-Off Delay Time ^c | $t_{d(off)}$ | | | 17 | 25 | |
| Fall Time ^c | t_f | | | 30 | 45 | |
| Source-Drain Diode Ratings and Characteristic ($T_C = 25\text{ }^\circ\text{C}$) | | | | | | |
| Pulsed Current | I_{SM} | | | | 45 | A |
| Diode Forward Voltage ^b | V_{SD} | $I_F = 15\text{ A}, V_{GS} = 0\text{ V}$ | | 0.9 | 1.5 | V |
| Source-Drain Reverse Recovery Time | t_{rr} | $I_F = 15\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 55 | 85 | ns |

Notes:

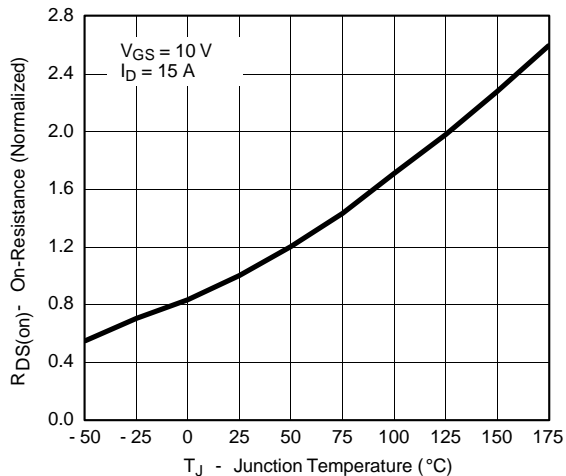
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

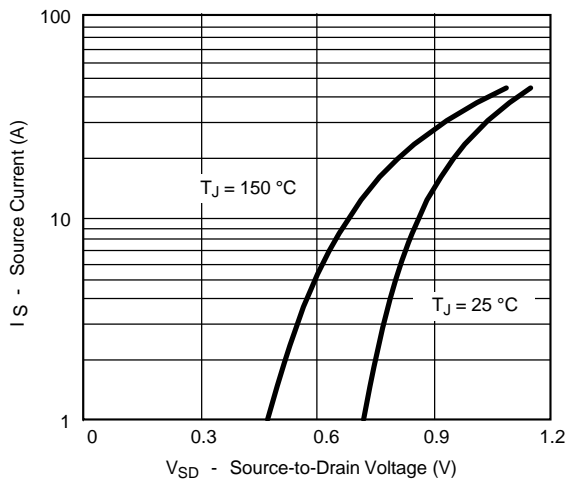
TYPICAL CHARACTERISTICS (25 °C unless noted)



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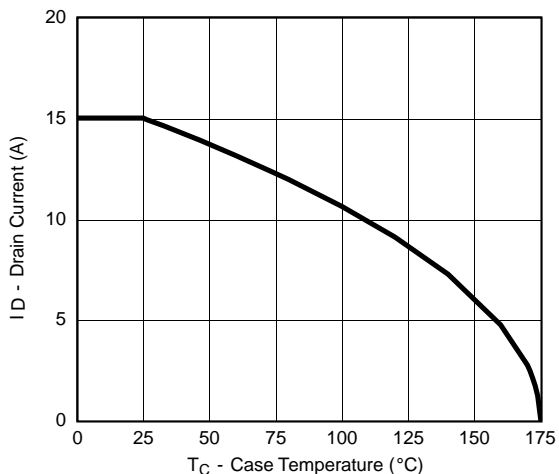


On-Resistance vs. Junction Temperature

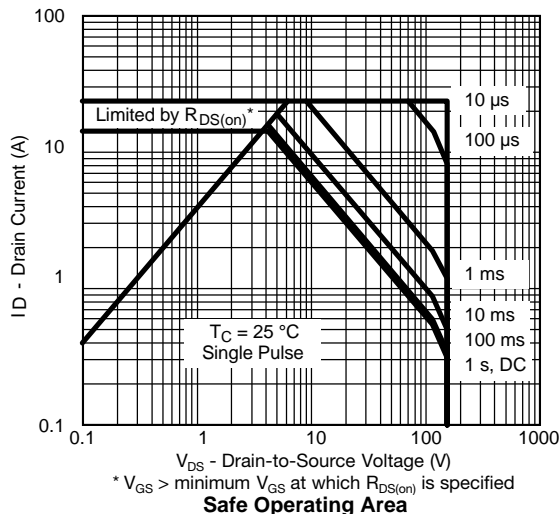


Source-Drain Diode Forward Voltage

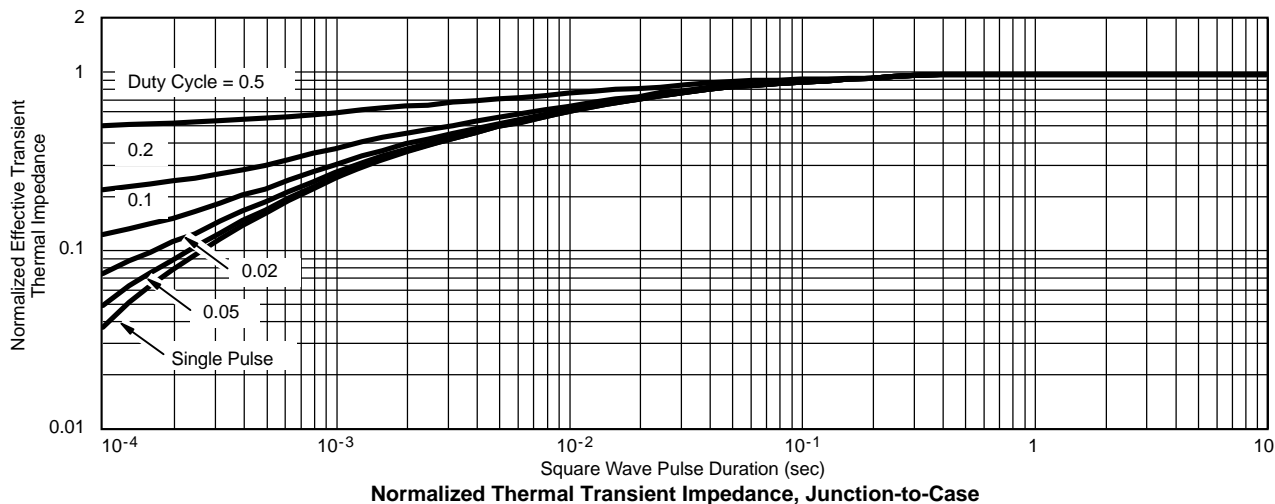
THERMAL RATINGS



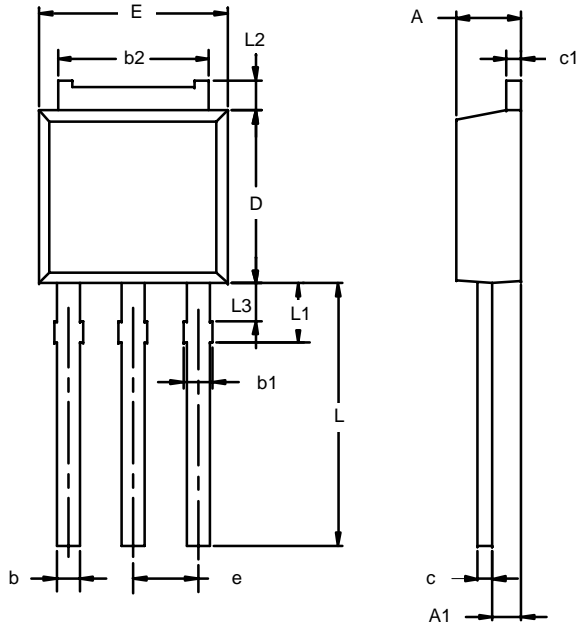
Maximum Avalanche Drain Current vs. Case Temperature



*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area**



TO-251AA (DPAK)



Note: Dimension L3 is for reference only.

| Dim | MILLIMETERS | | INCHES | |
|---|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 2.21 | 2.38 | 0.087 | 0.094 |
| A1 | 0.89 | 1.14 | 0.035 | 0.045 |
| b | 0.71 | 0.89 | 0.028 | 0.035 |
| b1 | 0.76 | 1.14 | 0.030 | 0.045 |
| b2 | 5.23 | 5.43 | 0.206 | 0.214 |
| c | 0.46 | 0.58 | 0.018 | 0.023 |
| c1 | 0.46 | 0.58 | 0.018 | 0.023 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| E | 6.48 | 6.73 | 0.255 | 0.265 |
| e | 2.28 BSC | | 0.090 BSC | |
| L | 8.89 | 9.53 | 0.350 | 0.375 |
| L1 | 1.91 | 2.28 | 0.075 | 0.090 |
| L2 | 0.89 | 1.27 | 0.035 | 0.050 |
| L3 | 1.15 | 1.52 | 0.045 | 0.060 |
| ECN: S-03946—Rev. E, 09-Jul-01 DWG: 5346 | | | | |

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